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Author(s)	Hosono, Akira; Masubuchi, Yuji; Higuchi, Mikio et al.
Citation	Solid state sciences, 144, 107310 https://doi.org/10.1016/j.solidstatesciences.2023.107310
Issue Date	2023-10
Doc URL	https://hdl.handle.net/2115/95977
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Type	journal article
File Information	Solid State Sci. 144 107310.pdf



Ferroelectric BaTaO₂N perovskite — Towards structure-property relationship study on high-quality crystals and ceramics prepared with the aid of liquid phase

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Abstract

The ternary metal oxynitride compound, perovskite-type BaTaO₂N, has been a subject of interest for solid-state physicists and chemists. The notable dielectric property has been reported in a centrosymmetric average structure although the anisotropic anion configuration is preferable in *cis*-TaO₄N₂ octahedra around Ta⁵⁺ with d⁰ electron state. Either single crystals or sintered ceramics in high quality is necessary to clarify the puzzle between the structure and property. Thin film studies are sometimes misleading and confusing. This report reviews the preparation of BaTaO₂N in high quality from the viewpoints of its crystal growth in a liquid phase, sintering in a thick ceramic form, and low-temperature and short time sintering with a liquid phase additive to obtain the high-

quality samples for investigation of the structure-dielectric property relationship.

Keywords: Perovskite-type oxynitride; dielectric; single crystal; ceramics

1. Introduction

Over the last 40 years, a variety of oxynitride compounds with perovskite-type crystal structure have been synthesized. Many examples, such as $AETaO_2N$ ($AE = Ca, Sr, Ba$), $AENbO_2N$, $LnTaON_2$ ($Ln = \text{lanthanoid}$), $LnTiO_2N$, $NdVO_2N$, non-stoichiometric compounds, $SrMo(O,N)_3$, $BaW(O,N)_3$, $BaTi(O,N,\square)_3$, where $\square$ is anion vacancy, and a series of Ruddlesden-Popper-type layered perovskites have been reported [1-20]. The powder synthesis of one typical material, $BaTaO_2N$, was firstly reported in 1986 [21]. It took a little longer for the potential of this material as a dielectric material to be revealed because its space group had long been considered to be centrosymmetric $Pm\bar{3}m$ [3]. The local crystal structure of $BaTaO_2N$ was furtherly characterized using infrared spectroscopy in 1995 [22]. Some deviation from the centrosymmetric cubic perovskite was observed in a presence of several unattributable peaks but there was no evidence of a soft mode in $BaTaO_2N$ polycrystalline pellet.

In 2004, unusually large relative dielectric constant values of $BaTaO_2N$ ($\epsilon_r \approx 4600$) and $SrTaO_2N$ ($\epsilon_r \approx 3000$) over the temperature range of 180–300 K were reported

for their powder compacts annealed at 1050 °C under ammonia flow. Its relative density (RD) was approximately 55% [23]. However, the centrosymmetric space groups of these materials ($Pm\bar{3}m$ for BaTaO₂N and $I4/mcm$ for SrTaO₂N) are contradictory to such large dielectric constant values. Theoretical and crystallographic studies were undertaken to obtain a consistent explanation of polar crystal structures. Local crystallographic anisotropy due to a *cis*-type nitrogen configuration in TaO₄N₂ octahedra has been one important factor to introduce spontaneous polarization into oxynitride perovskites [6,14,24-31]. The local structure of BaTaO₂N examined using transmission electron microscopy (TEM), extended X-ray absorption fine structure, and neutron pair distribution functions suggested several different distances in Ta-O and Ta-N respective bonds [24-26]. These results suggested that each Ta atom is slightly displaced in one direction from its average centrosymmetric position in the cubic perovskite to form one dimensional (linear) polar nano regions (PNRs) [25]. A recent report of secondary harmonic wave generation (SHG) and piezoelectric response from BaTaO₂N microcrystals also supports this hypothesis for the presence of locally non-centrosymmetric structural units in the centrosymmetric average crystal structure [32].

First-principles calculation of structure of BaTaO₂N suggested the local symmetry breaking due to a displacive disorder in Ta-O and Ta-N distances [33]. Density

functional theory (DFT) calculations of both SrTaO₂N and BaTaO₂N with a *cis*-type anion configuration model indicated the formation of helical coil-like polar Ta-N-Ta-N chains with various lengths and directions [27]. In relation to these locally distorted structure models, relaxor-like ferroelectric properties in these oxynitride perovskites were expected. Additional theoretical investigations on each crystal structure of the oxynitride perovskites have been conducted by several independent researchers. Structural optimizations of CaTaO₂N, SrTaO₂N, and BaTaO₂N were performed using total-energy calculations and phonon-computations [28]. It should be noted that all the oxynitrides were determined to be stable in the orthorhombic *Pnma* space group, unlike their previous powder neutron and X-ray diffraction (XRD) results where centrosymmetric models *I4/mcm* for SrTaO₂N and *Pm3m* for BaTaO₂N were assumed [3,4,23]. Further structural optimization for BaTaO₂N indicated that the most favorable space group is non-centrosymmetric *Pmc2₁* [28], which is consistent with the observation of ferroelectricity in BaTaO₂N crystals, as discussed in the next section [32]. This result has been extended to a series of oxynitride perovskites, such as *LnTaON₂* (*Ln* = La, Ce, Pr) and CaTaO₂N [29]. However, it is challenging to detect a polar phase of oxynitride perovskites because each domain is too small to induce the diffraction of irradiated beams. Therefore, profile refinements of powder diffraction data tend to converge to averaged high-symmetry space

groups.

Concurrently with crystal structure investigations, many experimental trials were performed to fabricate dense ceramics and thin films to confirm the dielectric properties, as mainly reviewed for SrTaO_2N [34]. However, there had been a number of technical problems to be solved to unambiguously confirm BaTaO_2N as a ferroelectric material, due to difficulty in sintering while maintaining its stoichiometry. There has been much less the fabrication of single crystals than the ceramics. The main difficulty in obtaining dense oxynitride ceramics and single crystals is their thermal instability. The decomposition behavior of BaTaO_2N is strongly dependent on the heating atmosphere, as depicted in the thermogravimetry (TG) curves of Figure 1 [35]. BaTaO_2N begins to release a part of its nitrogen at approximately 920 °C, and its chemical composition is changed to $\text{BaTaO}_2\text{N}_{0.85}$ with a nitrogen-deficient perovskite-type structure. The chemical composition was estimated from the oxygen and nitrogen contents measured by oxygen/nitrogen combustion analyzer and the nitrogen deficiency was almost consistent with the weight loss in TG measurement. No oxygen release was detected, and further decomposition was almost suppressed in a nitrogen atmosphere, whereas BaTaO_2N was completely decomposed to a mixture of $\text{Ba}_5\text{Ta}_4\text{O}_{15}$, BaTa_2O_6 , and Ta_2N under helium flow. Quite similar decomposition behavior was reported for the analogous compound

SrTaO₂N [16,36,37]. A high-pressure nitrogen atmosphere was directly applied to investigate the nitrogen release from the oxynitride perovskites using hot isostatic pressing [38]. A SrTaO₂N powder compact lost some nitrogen at 1400 °C even under 190 MPa of nitrogen to form a nitrogen-deficient perovskite, SrTaO₂N_{0.7}, which is similar to the decomposition of BaTaO₂N at ambient pressure. This result indicates the formation of nitrogen-deficient perovskite-type oxynitrides is inevitable during high-temperature heating above 920 °C. For the perovskite-type oxynitride, high-temperature sintering and crystal growth from a melt requires an additional process to recover the nitrogen-loss or, conversely, a low temperature process below the decomposition temperature is required.

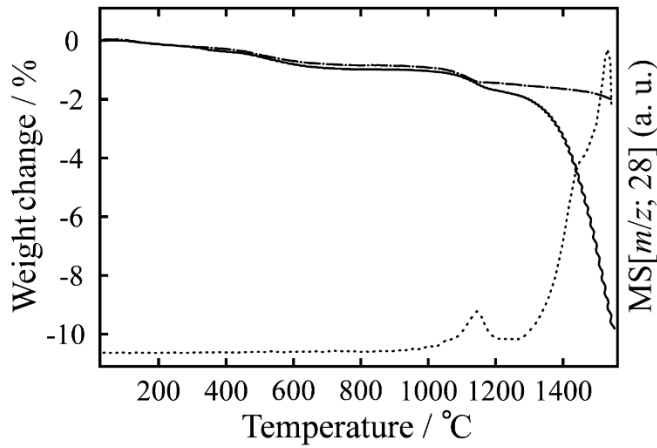


Figure 1. Weight loss of BaTaO₂N oxynitride perovskite powder during heating in a helium (solid line) or nitrogen (dot-dashed line) atmosphere and nitrogen evolution detected by mass spectrometry (helium atmosphere, dashed line). The heating rate in both atmospheres was 20 °C/min [35]. Reproduced with permission from ref. 35. Copyright

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This paper provides a research history of the crystal growth and sintering of BaTaO₂N ferroelectrics with an assistance of a liquid phase towards further investigations on the relation between the crystal structure and dielectric property [32,39,40]. Microcrystal preparation of BaTaO₂N using a low temperature flux is reviewed and its ferroelectric characteristics are discussed. High temperature sintering using a sintering additive followed by nitridation in an ammonia atmosphere is also applied for a thick powder film prepared by electrophoretic deposition (EPD). Sintering at low-temperature with short duration, which was performed in spark plasma sintering (SPS) equipment, is also discussed for the fabrication of a sintered body without nitrogen deficiency.

2. Ferroelectric BaTaO₂N microcrystals

Ferroelectricity does not appear on BaTaO₂N in cubic perovskite-type structure. Local symmetry breaking is needed on the averaged long-range crystal structure induced by the O/N *cis*-type configuration around Ta. The symmetry breaking exhibits ferroelectric and piezoelectric characteristics in the perovskite-type BaTaO₂N. Dense ceramics and single crystal of BaTaO₂N demonstrated polar switching under applying high electrical voltage. In this section, single crystal growth of BaTaO₂N in a BaCN₂ flux

is reviewed and ferroelectric behavior of the crystal is discussed.

2. 1 Fluxes for metal nitrides and oxynitride crystals

Solid-state sintering is not applicable to a BaTaO₂N powder compact below 920 °C, at which point it begins to release part of the nitrogen to become an *n*-type semiconductor losing insulating property. Liquid phases that act as a solvent of BaTaO₂N while maintaining its anion contents would thus be beneficial for its crystal growth or liquid-phase sintering.

There are only a limited number of reports on crystal growth of metal nitrides due to a lack of the knowledge on appropriate fluxes. Na metal and NaN₃ [41,42], Li₃N [43], and Ca₃N₂ [44] are well known fluxes in crystal growth of typical metal nitrides. Melts of Li₃BN₂ and alkaline-earth boron nitrides are fluxes for the productions of hexagonal- and cubic-boron nitride (BN) crystals [45,46]. Flux selection is much more difficult in metal oxynitrides than nitrides. The oxygen/nitrogen molar ratio in target materials needs to be maintained under low oxygen partial pressure atmospheres at high temperature.

Crystal growth trials of transition metal oxynitrides are recently becoming more familiar to solid-state chemists and physicists. Grain growth of relatively large TaON

crystal samples under gigapascal pressure was reported using LiCl flux [47]; however, growth was conducted at 1400 °C, whereby oxygen loss resulted in electrical conductivity. Post-annealing was necessary to compensate for the loss of oxygen, just as in the reports on the high-temperature sintering of SrTaO₂N and BaTaO₂N [35-37]. To maintain the nitrogen stoichiometry of BaTaO₂N and avoid a partial formation to semiconductor, dissolution and recrystallization processes must be conducted at temperatures lower than that of nitrogen loss (920 °C).

Submicron crystals of perovskite-type BaTaO₂N and LaTiO₂N with cubic shape were synthesized using KCl and K₂MoO₄ as fluxes [48,49]. The ammonothermal method has also been employed to grow micron-sized oxynitride perovskite crystallites such as *ABO₂N* (*A* = Sr, Ba, *B* = Nb, Ta) [50], *LnTaON₂* (*Ln* = La, Ce, Pr, Nd, Sm, Gd) [51], and LaNbON₂ [52]. It should be noted that the residual potassium needs to be removed. Fluxes are more favorable to have similar chemical composition to target materials.

2. 2 Crystal growth of BaTaO₂N in a BaCN₂ flux

Metal carbodiimides are ionic crystals composed of metal cations and symmetric [N=C=N]²⁻ anionic unit, which is distinct from asymmetric cyanamide anion [N-C≡N]²⁻. Alkaline-earth metal carbodiimides were synthesized by heating their metal

carbonate powder under flowing ammonia at 700–1000 °C [53-56]. Thermochemical experiments in a nitrogen atmosphere indicated the tetragonal phase of BaCN₂ has a melting point of 910 °C [53,57], which is slightly below the nitrogen release point of BaTaO₂N (920 °C) [35].

Reddish BaTaO₂N and white BaCN₂ powders were mixed and heated in a dry nitrogen atmosphere. Microcrystals of BaTaO₂N were obtained by heating the mixture at 910 °C with successive slow cooling. The size of crystals extracted by nitric acid leaching became larger with an increase in the amount of BaCN₂. The largest crystal size was 3.1 μm with 46 mol% BaCN₂ flux, as shown by the scanning electron microscopy (SEM) images in Figure 2 [32]. The stoichiometric chemical composition was confirmed on a single grain larger than 2 μm by electron probe micro analysis (EPMA) of BaTaO₂N crystals, combustion analyses, and vivid red color shown in Figure 2(e-2) [2]. Further addition of BaCN₂ yielded only small BaTaO₂N crystallites that were less than 100 nm in size because of the full dissolution and successive nucleation of BaTaO₂N from the melt.

High-resolution TEM observation confirmed the cubic or cuboid grains are single crystals of BaTaO₂N perovskite, as shown in the selected area electron diffraction (SAED) pattern in Figure 3(b). Further observation around interface between the BaTaO₂N crystals and solidified BaCN₂ flux suggested Ruddlesden-Popper-type

$\text{Ba}_2\text{TaO}_3\text{N}$ acts as a reaction intermediate. The dissolved BaTaO_2N formed Ba-rich matrix with molten BaCN_2 . And then, BaTaO_2N recrystallized at its outermost surface of the surrounding $\text{Ba}_2\text{TaO}_3\text{N}$. The process proceeds during the cooling and condensation of solutes due to a flux loss in the heating [32,53].

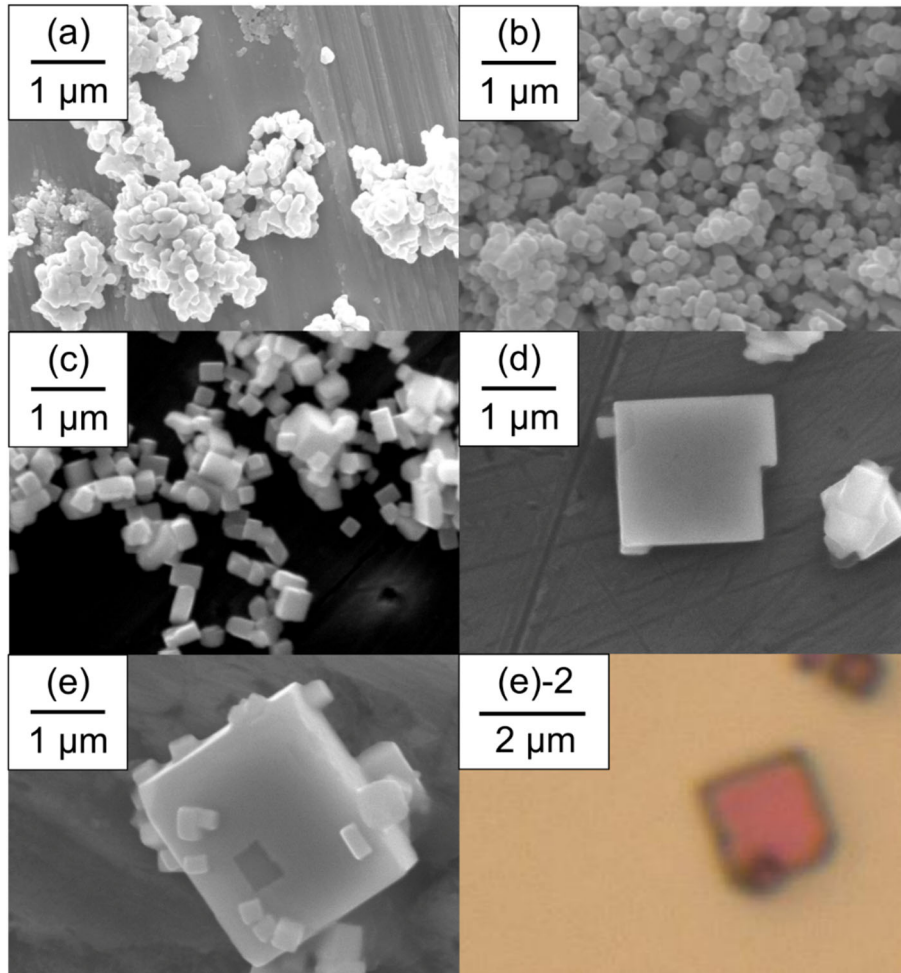


Figure 2. SEM micrographs of BaTaO_2N particles: (a) As-prepared ammonolysis product; (b–e) products generated in the flux at 910 °C for 30 min with 17, 22, 36, and 46 mol% BaCN_2 , respectively, after cooling at 1.8 °C/h and acid/water washing. [(e)-2] optical micrograph of the product in (e) [32]. Reproduced with permission from ref. 32.

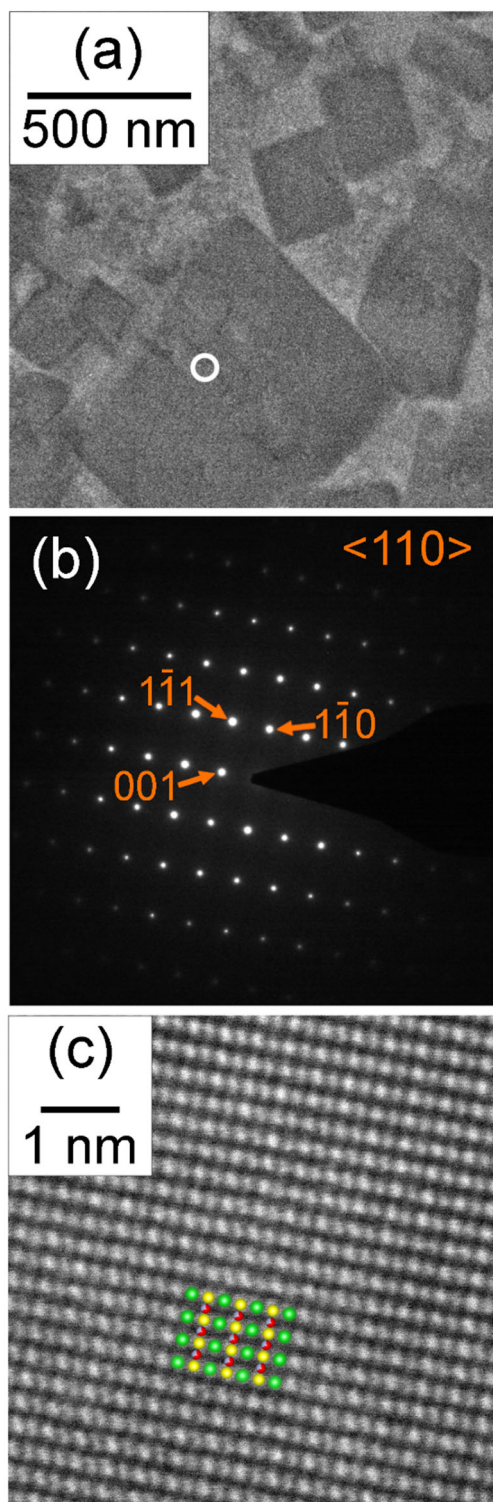


Figure 3. (a) TEM bright-field image of a thin specimen of BaTaO₂N crystals with solidified BaCN₂ flux. (b) SAED image of the encircled area in (a). (c) High-magnification high-angle annular dark-field-scanning transmission electron microscopy (HAADF-STEM) image of the area encircled in (a). Green, yellow, and red circles in (c) indicate Ba, Ta, and O/N anions, respectively [32]. The crystal structure model was drawn using the crystallographic imaging software VESTA [58]. Reproduced with permission from ref. 32. Copyright 2019 American Chemical Society.

2. 3 Piezoresponse of BaTaO₂N microcrystals

The piezoelectricity of BaTaO₂N crystals was investigated using piezoresponse force microscopy (PFM) technique [32]. A mono-layered capacitor structure of micron-sized BaTaO₂N crystals was fabricated. A top electrode of Pt is necessary to exclude the negative effect of electrostatic force, which disturbs a clear distinction between intrinsic piezoelectricity of BaTaO₂N crystals and extrinsic effects [59-61]. Electrical insulation was significantly improved in the BaTaO₂N crystals compared to the ceramics that were sintered at high temperature and then nitrified in an ammonia flow [62]. Significant electrical insulation of the crystals made it possible to apply high electrical voltage without current leakage.

Relatively strong electrical field was required for the BaTaO₂N crystals to switch their polarization direction and demonstrate their ferroelectricity [32]. The butterfly-type piezoresponse curve shown in Figure 4(b) and the ferroelectric phase hysteresis graph in Figure 4(c) suggest approximately 250 kV/cm of its coercive electrical field at 120 °C, which may originate from strong covalent bonding due to the presence of nitrogen in the crystal structure. No butterfly-like piezoresponse was obtained at room temperature because the polarization phase alternation was more difficult to change at ambient temperatures [63]. Polarization phase in PNRs is more easily altered at high temperatures as reported in typical relaxor ferroelectrics like Pb(Mg_{1/3}Nb_{2/3})O₃ [64]. The polarization phase alternation in BaTaO₂N at high temperature suggests the ferroelectric properties of BaTaO₂N perovskite is conjunction to PNRs. Simple cubic perovskite-like SAED pattern shown in Fig. 3(b) was obtained from the as-grown BaTaO₂N microcrystal, because the non-centrosymmetric polar domain was too small to induce the diffraction and the polarization direction of each domain was randomly distributed in the crystal without polarization. Single crystal of BaTaO₂N after polarization should be used in diffraction experiments to investigate the non-centrosymmetric crystal structure.

In conclusion, BaTaO₂N was confirmed to be a ferroelectric material by PFM measurements of microcrystals. Examinations of their polarization (*P*)-electrical field (*E*)

hysteresis and capacitance values for application as dielectrics remains a challenge because of the weak electrical current signal generated via the small electrodes on the microcrystals. Advances of the techniques for crystal growth and a sintering of insulating ceramics are thus urgently required.

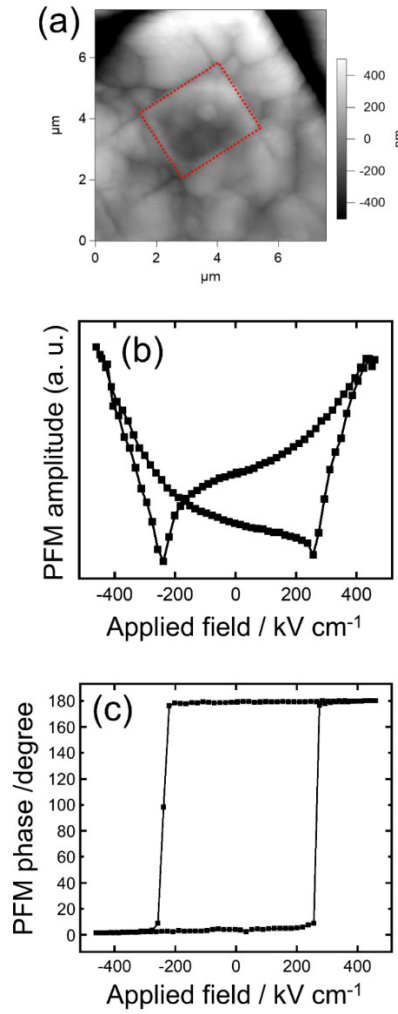


Figure 4. (a) AFM topographical image of a BaTaO_2N crystal (indicated by the dotted red square), (b) piezoresponse amplitude curve obtained at 120°C , and (c) corresponding ferroelectric phase signal graph [32]. Reproduced with permission from ref. 32. Copyright

3. High temperature sintering and ammonia annealing

PFM measurement using a single crystal of BaTaO_2N confirmed the ferroelectricity and superior electrical insulating properties. Bulk ceramics of BaTaO_2N will enable an evaluation of capacitance and practical applications. However, high-temperature sintering of BaTaO_2N powder compacts results in the formation of semiconductor bulk ceramics that have lost the original insulating properties. In this section, the sintering process of thermally unstable BaTaO_2N is discussed in relation to the use of boron oxide as a sintering additive.

3. 1 High temperature sintering of BaTaO_2N

Preliminary sintering studies had been performed without any special care about the thermal release of nitrogen from the oxynitrides. The thermal stability, sinterability, and the electrical and piezoelectric properties of BaTaO_2N polycrystalline ceramics were investigated following the precedent examples of the SrTaO_2N ceramics [16,36,37,65]. To achieve more reliable dielectric constants, several trials were performed to fabricate ceramics with RDs that were higher than those reported by Kim et al. (55%) [23]. Special care to maintain the sintering atmosphere at low oxygen partial pressure is necessary to

operate BaTaO₂N powder at high temperature, because tantalum-containing oxynitride perovskites are easily oxidized to a mixture of their component metal oxides at around 400 °C [66,67]. The decomposition behavior of BaTaO₂N is strongly dependent on the heating atmosphere, as shown by the TG curves in Figure 1 [35].

Solid-state sintering procedures are hardly applicable to metal oxynitrides due to their extremely small diffusion constants; therefore, high-temperature processes and the use of sintering additives are generally necessary to obtain dense ceramics. BaTaO₂N is thermally unstable; therefore, there is a technical difficulty in sintering stoichiometric BaTaO₂N ceramics at high temperatures. A two-step process has been employed that involves high-temperature sintering of nitrogen-deficient BaTaO₂N_{0.85} and subsequent annealing in an ammonia atmosphere to replace the lost nitrogen. To obtain ceramics that maintain the perovskite-type phase requires that BaTaO₂N green-powder compacts be sintered in an inert atmosphere, e.g., pure nitrogen.

To compensate for a slight loss of Ba during high-temperature sintering and avoid the formation of TaN impurities, 2.5–5.0 wt% of BaCO₃ was added to BaTaO₂N [35]. During sintering, reddish powder compacts were placed into a BN polycrystalline crucible and held in a pure nitrogen atmosphere at 0.2 MPa. The sample color was changed to black, i.e., changed to a semiconductor, similarly to SrTaO₂N, which partially

loses nitrogen to form $\text{SrTaO}_2\text{N}_{0.7}$ during sintering [16,36,37,65] as the as-sintered ceramics were *n*-type semiconductors because of the partial reduction of Ta^{5+} to $\text{Ta}^{4+}/\text{Ta}^{3+}$. Particle necking and densification did not proceed below 1400 °C and the maximum RD value of nitrogen deficient $\text{BaTaO}_2\text{N}_{0.85}$ was 93.0% [35]. The contribution of a Sr-B-O ternary amorphous phase in the grain boundaries and triple points was recently reported for the sintering of $\text{SrTaO}_2\text{N}_{0.7}$ with a B_2O_3 sintering additive at 1400 °C [68]. It can thus be inferred that a similar secondary phase could behave as a sintering reagent for $\text{BaTaO}_2\text{N}_{0.85}$.

The reddish color on the sample was recovered after heating the $\text{BaTaO}_2\text{N}_{0.85}$ ceramics under ammonia flow at 1000 °C [35]. The homogeneity of annealed ceramics is dependent on the RDs of the $\text{BaTaO}_2\text{N}_{0.85}$ ceramics. The entire porous bulk (RD $\leq$ 74.6%) became red, while the interiors of dense samples remained black (semiconductor) because ammonia or related nitriding reagents could not diffuse into the highly densified microstructure [35,62].

3. 2 Thick film of dense BaTaO_2N ceramic sintered with B_2O_3 additive

Dense ceramics of $\text{BaTaO}_2\text{N}_{0.85}$ were only nitrided in a thin surface layer with a thickness of approximately 10 μm . The surface of the thin layer recovered its nitrogen

content and electrically insulating properties after annealing in ammonia flow. Therefore, thick films of dense oxynitride perovskite ceramic with several tens of micrometers in thickness are expected to achieve both high RD and fully nitridation even after long-term annealing in ammonia. EPD was employed to fabricate thin films of ceramic powder compacts from a colloidal suspension [69,70]. The thickness and microstructure of the powder compacts can be controlled by tuning the deposition conditions, such as the suspension concentration, deposition time, and applied voltage. Powder compacts with a thickness of approximately 100 μm were fabricated from a mixture of BaTaO_2N and a BaCO_3 additive using the EPD method. The BaCO_3 additive compensates for the small amount of Ba loss that occurs during high-temperature sintering [35]. The powder compacts were placed in an alumina crucible with/without a small amount of B_2O_3 powder additive located in the crucible separate from the powder compacts and then sintered at 1400 $^\circ\text{C}$ for 4 h in a N_2 atmosphere at 0.2 MPa. B_2O_3 has been reported as a sintering additive together with SrCO_3 for SrTaO_2N to form a Sr-B-O liquid phase during sintering [68]. The effect of the B_2O_3 additive on the sintering of $\text{BaTaO}_2\text{N}/\text{BaCO}_3$ was also investigated by the supply of B_2O_3 to the powder compacts via the vapor phase. The sintered thick films of the $\text{BaTaO}_2\text{N}_{0.85}$ were black in color and electrically conducting due to the nitrogen loss during high-temperature sintering. To recover the nitrogen content

and electrical insulating properties, the sintered ceramics were subsequently annealed at 950 °C for 100 hours in a NH₃ flow of 100 mL/min.

A single-phase perovskite structure was observed for the ceramic sintered without B₂O₃, and a few secondary phases also appeared for the product sintered with the B₂O₃ additive. The B₂O₃ reacted with a small amount of Ba in the powder compact and Ta-rich impurity phases appeared in the sintered ceramic. Sintering of SrTaO₂N with B₂O₃ also formed nitrogen deficient SrTaO₂N_{0.75} contaminated with TaO_{0.9} [68]. SEM images of the fracture surfaces of the sintered ceramic show a dense microstructure for the product sintered with B₂O₃ (Figure 5(a)). In contrast, the ceramic sintered without B₂O₃ was porous (Figure 5(b)), but the grain size was larger than that sintered with B₂O₃. The RD values for BaTaO₂N sintered with and without the B₂O₃ additive were 92% and 78%, respectively. The improved sinterability could be understood by a formation of barium borate liquid phase [71], similarly to the case of SrTaO₂N sintering with B₂O₃ [68]. The smaller grains obtained by sintering with B₂O₃ resulted from sintering with a small amount of liquid phase and for a short duration, before reaching the grain growth step in the liquid-phase sintering process. Grains larger than 1 μm were formed together with small grains by an increase in the sintering time from 4 to 8 h or by increase in the temperature to 1420 °C. On the other hand, sintering without B₂O₃ corresponded to solid-

phase sintering and grain growth was accelerated by nitrogen deficiency to form large grains. The B_2O_3 additive improved the sintering of $BaTaO_2N$ similar to the case in $SrTaO_2N$.

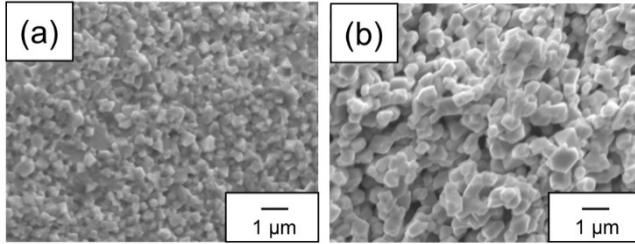


Figure 5. SEM images of fracture surfaces of sintered $BaTaO_2N$ ceramics at 1400 °C for 4 h (a) with B_2O_3 and (b) without B_2O_3 . Reproduced with permission from ref. 39. Copyright 2023 Elsevier.

The thick ceramic film sintered at 1400 °C for 4 h with the B_2O_3 additive was annealed in ammonia flow at 950 °C for long duration to compensate for the nitrogen deficiency that developed during the high-temperature sintering. Sample color gradually changed from black to red with increasing the annealing time and the nitrified area extended from the outer surface to the interior as shown in Figure 6. Full nitridation was confirmed by the red color of the sintered product after annealing for 100 h, as shown in Fig. 6(d), which was almost the same color as the green powder compact (Fig. 6(a)). Recovery to the single phase of $BaTaO_2N$ perovskite was also verified by XRD

measurement.

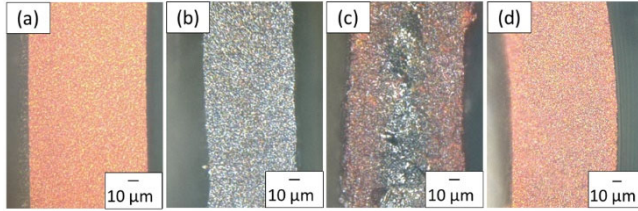


Figure 6. Optical images of cross sections (a) BaTaO₂N powder compact sintered with B₂O₃, and the resultant ceramic after annealing in ammonia flow at 950 °C for (b) 0 h, (c) 60 h, and (d) 100 h. Reproduced with permission from ref. 39. Copyright 2023 Elsevier.

3.3 Dielectric properties of the post-ammonolysis products

The dielectric properties of BaTaO₂N ceramics sintered at 1400 °C for 4 h after nitridations at 950 °C for 0, 60 and 100 h are shown in Figure 7. Nitrogen-deficient BaTaO₂N_{0.85} ceramics without a subsequent nitridation treatment show large relative dielectric constants above 30,000 with large dielectric loss values of 0.6-1. Both the large dielectric constant and loss can be explained by the semiconducting nature of the black sintered ceramic. After nitridation for 60 h, only the surface part of the thick ceramic was nitrided to recover the original red color, as shown in Figure 6(c). The dielectric constant decreased to values of several hundred, and the dielectric loss also decreased but was greater than 0.1. In previous research, the large dielectric constant was determined to

originate from residual semiconducting parts that were not fully nitrated due to the dense bulk structure [35]. The fully nitrated sample with a red interior as shown in Figure 6(d), exhibited dielectric constants of 530-320 at 1.2×10^2 - 10^6 Hz with $\tan \delta$ values of 0.15-0.05. These dielectric constants were larger and the dielectric losses were lower than those for bulk ceramics ($\epsilon_r = 300$ and $\tan \delta = 0.06$ at 10^5 Hz) with an RD of 73% [35]. The bulk ceramic with an RD of 73% was readily nitrated due to its porous structure, although some residual semiconducting material may possibly remain after the nitridation for a short duration. The temperature dependence of the dielectric properties is shown in Figure 7(b). An almost flat dependence was observed on the dielectric constant below 250 °C and the dielectric loss was maintained below 0.05. The slightly enhanced dielectric constant above 300 °C may be related to the semiconducting nature of the BaTaO₂N at high temperature. There is no clear trace of a phase transition of the BaTaO₂N ceramics with respect to the temperature, which indicates the ferroelectric characteristics remain up to 300 °C.

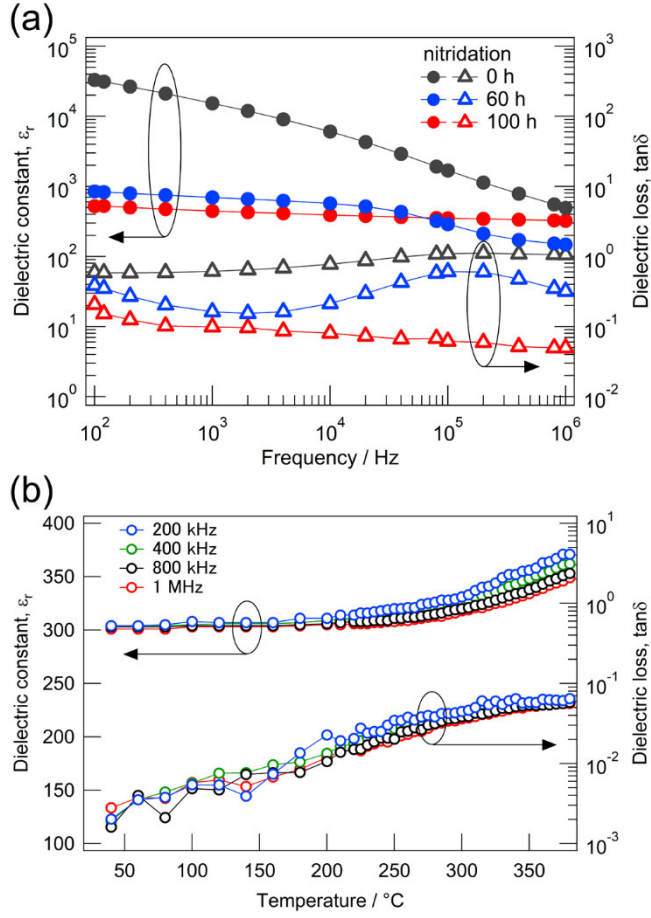


Figure. 7 (a) Frequency dependence of dielectric constants, ϵ_r , and dielectric loss, $\tan\delta$, for ceramics sintered at 1400 °C and annealed in ammonia at 950 °C. (b) Temperature dependence of ϵ_r , and dielectric loss, $\tan\delta$, for the dense ceramics annealed in ammonia at 950 °C for 100 h. (a) was reproduced with permission from ref. 39. Copyright 2023 Elsevier.

4 Sintering of BaTaO₂N using a molten BaCN₂ additive in SPS equipment

An ordinary sintering of BaTaO₂N at high temperature fabricated BaTaO₂N_{0.85}

dense ceramics with some nitrogen deficiencies. Both original nitrogen content and electrical insulation were recovered only on the ceramic surface as mentioned in section 3.1 and in the thick film as described in section 3.2. However long duration of the post-ammonolysis is required to obtain stoichiometric ceramic products. A BaCN_2 melt is used as a flux for the crystal growth of BaTaO_2N below 910°C , which is slightly below the decomposition temperature. In this section, rapid sintering of BaTaO_2N in low-temperature is discussed by using SPS equipment with a corporation of BaCN_2 melt as a sintering aid. Liquid phase sintering mechanism is investigated in relation to the amount of additive.

4. 1 Liquid phase sintering using SPS equipment

Direct sintering of BaTaO_2N ceramics without nitrogen loss is desired to simplify sample preparation to keep the electrical insulation properties compared to the high-temperature sintered product [35,39]. A BaCN_2 melt was useful to obtain polycrystalline BaTaO_2N ceramics in SPS equipment for short-term sintering under pressure to avoid the thermal decomposition of BaTaO_2N [40,72-76]. Simple SPS process has also been attempted for LaTiO_2N oxynitride perovskite in a nitrogen atmosphere at $1250\text{--}1400^\circ\text{C}$ [77]. The products were black dense ceramics suggesting that they were

electrical conductive, and the perovskite-type phase was partially decomposed to a mixture of La_2O_3 and TiN . They were not stoichiometric LaTiO_2N and contaminated with their decomposition products. It is most probable that LaTiO_2N itself was not sintered, but that by-products after phase decomposition or a perovskite with high anion deficiency assisted the bulk densification. Additive sintering using a flux is a sensible strategy to lower the sintering temperature and shorten the densification time to overcome the difficulties.

Powder mixtures of BaTaO_2N and 0–20 wt% of BaCN_2 were sintered into a 1 mm-thick and 10 mm diameter disk using an SPS equipment. Prior to sintering, additive-free BaTaO_2N mother powder was placed between the $\text{BaTaO}_2\text{N}/\text{BaCN}_2$ mixed powder compact and the carbon die to avoid carbon contamination via molten BaCN_2 . Uniaxial mechanical pressure was applied to the samples up to 100 MPa and the carbon die was then heated to approximately 900 °C at a rate of 200 °C/min and held for 1–10 min under a nitrogen atmosphere.

All the ceramic products were red in color, which implies a negligible amount of nitrogen deficiency. No densification was observed for the additive-free BaTaO_2N powder. The powder mixtures containing some amount of BaCN_2 were rapidly densified to RDs higher than 66.5%. The effects of the amount of BaCN_2 , the applied pressure, and

the time held at 900 °C on the RD values are shown in Figures 8(a) and 8(b). The BaCN₂ additive is obviously effective for rapid densification compared to high-temperature ordinary sintering that forms nitrogen-deficient BaTaO₂N_{0.85}.

The samples sintered with 7 wt% BaCN₂ tended to show relatively low RD values as shown in Figure 8. Systematic change in RD was observed only on the sintering with 5 wt% BaCN₂. The solid particles were closer to each other because there was not too much molten BaCN₂. In this case the ceramic products become a little denser with a help of bulk diffusion through the flux. Too much amount of the BaCN₂ flux does not enhance the densification. Excess flux run out from the mixture to the powder bed. Some penetration of molten BaCN₂ into the additive-free BaTaO₂N powder beds was detected by analysis of the Ba/Ta molar ratios after SPS.

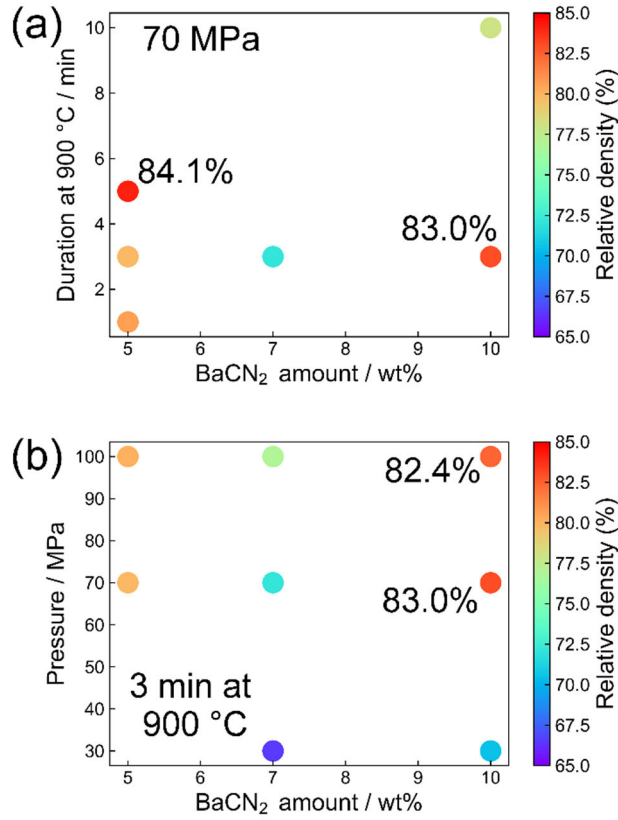


Figure 8. Color map of the RDs of BaTaO₂N ceramics as a function of (a) time held at 900 °C and the amount of BaCN₂ additive sintered at 70 MPa pressure, and (b) applied uniaxial pressure with the amount of BaCN₂ additive sintered at 900 °C of 3 min. The plotted data are for the samples with stoichiometric nitrogen contents.

The effect of the applied mechanical pressure was also examined, and the results are shown in Figure 8(b). The RD values increased under pressure higher than 30 MPa. Molten BaCN₂ infiltrated between the BaTaO₂N particles to wet their particle surfaces under mechanical pressure. The RD values did not increase furthermore above 70 MPa,

because an excess amount of molten BaCN_2 was removed from the main $\text{BaTaO}_2\text{N}/\text{BaCN}_2$ powder compact to the upper and lower BaTaO_2N powder beds under excessively high pressure. The maximum RD value of the stoichiometric BaTaO_2N ceramics was 84.1%, which was obtained using 5 wt% BaCN_2 and a pressure of 70 MPa at 900 °C for 5 min.

4. 2 Sintering mechanism of BaTaO_2N with molten BaCN_2

The main crystalline phase in the SPS ceramics was perovskite-type BaTaO_2N and Ba-rich Ruddlesden-Popper-type $\text{Ba}_2\text{TaO}_3\text{N}$ appeared as a secondary phase similar to the crystal growth of BaTaO_2N with BaCN_2 [32]. Material diffusion is assisted by chemical reactions in which the perovskite oxynitride dissolves and recrystallizes from the molten BaCN_2 . Figure 9(a) shows a TEM bright-field image of a thin ceramic specimen with an RD of 80.7% obtained in SPS equipment and the primary particle size of as-prepared BaTaO_2N powder is shown in Figure 9(d). Grains in the ceramics are connected via thin boundaries and some voids are observed in the microstructure. Large pores in the ceramics are present (Fig. 9(a)) probably because the packing of starting powder was insufficient. Energy dispersive X-ray spectroscopy (EDS) compositional analysis was conducted at several points across a grain boundary, as shown in the

HAADF-STEM image (Figure 9(b)). The Ba/Ta molar ratio gradually increased from the grain interior to the exterior and the maximum value was at the triple point (point 4 in Figure 9(b)). Molten BaCN_2 spread out into a narrow grain boundary area due to the mechanical pressure and wetted the BaTaO_2N grain surface forming Ba-rich Ruddlesden-Popper phase. The BaCN_2 flux is concentrated in the triple points of solidified BaTaO_2N grains. Such Ba-rich constituents can sometimes be confined in the triple points of the grown BaTaO_2N grains as shown in Figure 9(c).

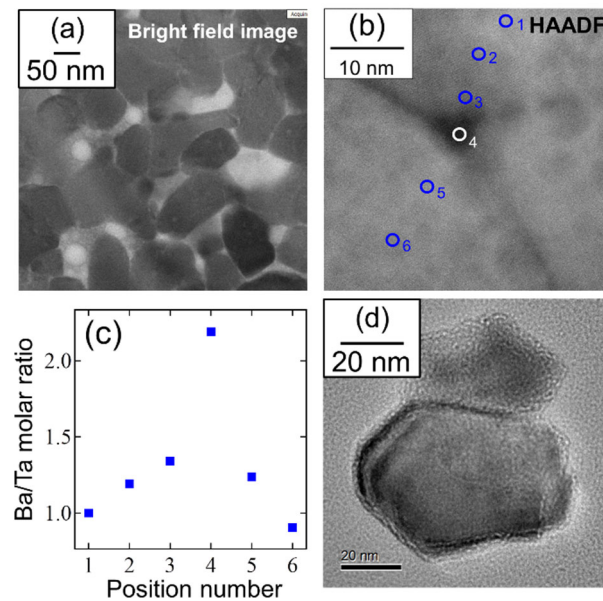


Figure 9. (a) TEM bright-field and (b) HAADF-STEM images of a BaTaO_2N ceramic specimen with an RD of 80.7%. (c) Ba/Ta molar ratios observed using EDS at several points indicated in (b). (d) Bright-field image of the as-prepared BaTaO_2N particles obtained by the ammonolysis [40]. Reproduced with permission from ref. 40. Copyright 2020 Elsevier.

4. 3 Electrical properties of the BaTaO₂N ceramics prepared in SPS equipment

The electrical properties of the BaTaO₂N ceramic sample with an RD of 79.8% were examined at room temperature over a frequency range of 10²–10⁶ Hz. Figure 10(a) shows a Cole-Cole plot with only a small part of a giant arc, which suggests electrically insulating characteristics, even without post-ammonolysis. Figure 10(b) shows a relative dielectric constant ϵ_r of 320 and a dielectric loss $\tan\delta$ of 0.04 at 10⁵Hz, which are comparable with the best values reported for a post-annealed ceramics thick film with an RD of 89% sintered at high temperature ($\epsilon_r = 300$ and $\tan\delta = 0.04$) [39]. These values for dielectric property suggest that partial nitrogen loss did not occur in the present sintering at 900 °C. The densification was possible below the temperature for nitrogen release from BaTaO₂N and around the melting point of BaCN₂.

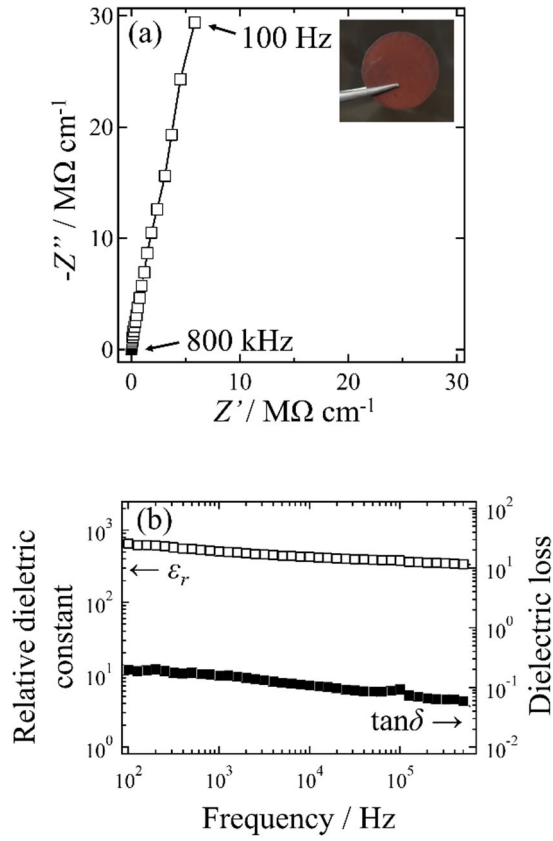


Figure 10. (a) Cole-Cole impedance plots and (b) dielectric properties of a BaTaO₂N ceramic (RD = 79.8%) as a function of frequency at room temperature. The inset in (a) shows a photograph of the polished ceramic surface [40]. Reproduced with permission from ref. 40. Copyright 2020 Elsevier.

In summary, BaTaO₂N powder was sintered at the lowest temperature (approximately 900 °C) among those sintering studies, using a BaCN₂ additive under mechanical pressure in SPS equipment to avoid partial nitrogen loss. BaTaO₂N grains were sintered each other through their dissolution and precipitation around their surfaces

in the BaCN_2 melt. A minor reaction product, Ba-rich Ruddlesden-Popper-type $\text{Ba}_2\text{TaO}_3\text{N}$, was present in the grain boundaries and triple points of the ceramics. Rapid heating and cooling processes in an SPS furnace were also effective to avoid partial nitrogen loss from BaTaO_2N crystal lattice. A maximum RD of 84.1% was observed for the BaTaO_2N ceramic with the original nitrogen content maintained. Further increase in the RD could be achieved by improvement of the starting BaTaO_2N powder contacts through a change in the morphology or through the use of an alternative flux with a lower melting point to allow for longer sample heating times for densification.

5. Conclusions and Future Outlook

During the last decade, perovskite-type BaTaO_2N has attracted much attention in solid state chemistry and physics. It was interesting as photocatalyst, lead-free pigment and dielectric materials. High quality sample was necessary to study its ferroelectricity in detail especially in the relation to crystal structure. Flux growth using BaCN_2 melt has been applied to BaTaO_2N and several micron-sized crystallites were produced without loss of the electrical insulation properties. Clear evidence of ferroelectricity with large coercivity was also obtained for small BaTaO_2N single crystals.

Dense ceramic thick films of nitrogen-deficient $\text{BaTaO}_2\text{N}_{0.85}$ were obtained by

high-temperature sintering of the compacts with a B_2O_3 additive by liquid-phase sintering. An electrically insulating dense ceramics of $BaTaO_2N$ with RD of 89% after annealing in ammonia showed a small temperature dependence of the dielectric constant of 300 and a dielectric loss below 0.05 up to 250 °C.

Another big advance was attained in low temperature sintering using $BaCN_2$ melt under mechanical pressure in SPS furnace. The $BaTaO_2N$ ceramic products were nitrogen loss-free maintaining the electrical insulation properties. It was possible to evaluate $BaTaO_2N$ ceramics as dielectric materials.

These high-quality products are now making a noticeable progress to study structure-property relation of the ferroelectricity in $BaTaO_2N$ [78]. Its non-centrosymmetric local structure needs to be clarified in the superficially centrosymmetric space group of $BaTaO_2N$. The spontaneous polarization can be estimated in the local structure. When the structure-property relationship is clarified, partial anion replacement will then make a great number of ternary materials to show novel and attractive functions. Authors believe that progress in high-quality processing will bring the well-sophisticated characterization of mixed anion products especially on $BaTaO_2N$ oxynitride perovskite.

Acknowledgments and Grants

The authors are grateful to the following for technical supports and invaluable

discussions: Professor Hisanori Yamane of Tohoku University, Japan for the crystal growth of oxynitrides, Professors Mitsuru Itoh and Shintaro Yasui of the Tokyo Institute of Technology, Japan for piezoelectric measurements of oxynitride crystals, Dr. Tetsuo Uchikoshi and Kento Ishii of the National Institute of Materials Science, Japan for electrophoretic deposition experiments.

We express gratitude to our former colleagues, Dr. S.-K. Sun of Foshan University, China. Valuable experimental results were obtained by our following alumni students: Dr. Y. -R. Zhang, Ms. D. Chen, Mr. D. Habu, Mr. M. Tadaki, Mr. D. Miyamoto, Mr. K. Koyama, and Mr. H. Takeuchi.

This research was partially financed by a Kakenhi Grant-in-Aids for Scientific Research (A) (No. 24245039) from the Japan Society for the Promotion of Science (JSPS) and as a part of the “Nanotechnology Platform” Program of the Japanese Ministry of Education, Culture, Sports, Science and Technology (MEXT) (Grant A-18-HK-00100). AH was supported by a JSPS research fellowship (Grant 19J10301). YM was also supported partly by a JSPS Grant-in-Aid for Scientific Research on Innovative Areas “Mixed anions” (Grant JP16H06439).

References

- [1] M. Jansen, H.P. Letschert, Inorganic yellow-red pigments without toxic metals, *Nature* 404 (2000) 980–982.
- [2] R. Aguiar, D. Logvinovich, A. Weidenkaff, A. Rachel, A. Reller, S.G. Ebbinghaus, The vast colour spectrum of ternary metal oxynitride pigments, *Dyes Pigment.* 76 (2008) 70–75.
- [3] F. Pors, R. Marchand, Y. Laurent, Structural study of BaTaO₂N and BaNbO₂N oxynitrided perovskites, *Mat. Res. Bull.* 23 (1988) 1447–1450.
- [4] S.J. Clarke, K.A. Hardstone, C.W. Michie, M.J. Rosseinski, High-temperature synthesis and structures of perovskite and n=1 Ruddlesden-Popper tantalum oxynitrides, *Chem. Mater.* 14 (2002) 2664–2669.
- [5] R. Marchand, F. Pors, Y. Laurent, Nouvelles perovskites oxynitrures de stoechiometrie ABO₂N (A = Lanthanide, B = Ti) et ABON₂ (A = Lanthanide, B = Ta ou Nb)”, *Ann. Chim. Fr.* 16 (1991) 553–560.
- [6] D. Habu, Y. Masubuchi, S. Torii, T. Kamiyama, S. Kikkawa, Crystal structure study of dielectric oxynitride perovskites La_{1-x}Sr_xTiO_{2+x}N_{1-x} ($x = 0, 0.2$), *J. Solid State Chem.* 237 (2016) 254–257.
- [7] G. Tobías, D.B. Porter, O.I. Lebedev, G.V. Tendeloo, J.R. Carvajal, A. Fuertes, Anion

ordering and defect structure in Ruddlesden-Popper strontium niobium oxynitrides, *Inorg. Chem.* 43 (2004) 8010–8017.

[8] G. Tobías Rossell, A. Fuertes, E. Canadell Casanova, Nuevos oxinitruros laminares de niobio y tántalo y sistemas relacionados : síntesis, cristalografía y estructura electrónica. Bellaterra: Universitat Autònoma de Barcelona, 2004. ISBN 8468891444. Tesi doctoral - Universitat Autònoma de Barcelona, <https://ddd.uab.cat/record/37099>, 2004 (accessed 5 January 2023).

[9] Y. Masubuchi, T. Hata, T. Motohashi, S. Kikkawa, Synthesis and crystal structure of K_2NiF_4 -type novel $Gd_{1+x}Ca_{1-x}AlO_{4-x}N_x$ oxynitrides, *J. Alloy Compds.* 582 (2014) 823–826.

[10] R. Marchand, Y. Laurent, J. Guyader, P. L’Haridon, P. Verdier, Nitrides and Oxynitrides: Preparation, Crystal Chemistry and Properties, *J. Eur. Ceram. Soc.* 8 (1991) 197–213.

[11] F. Chevire, A. Pallu, E. Ray, F. Tessier, Characterization of Nd_2AlO_3N and Sm_2AlO_3N oxynitrides synthesized by carbothermal reduction and nitridation, *J. Alloy Compds.* 509 (2011) 5839–5842.

[12] G. Liu, The synthesis, structure and characterization of $SrMoO_{2.6}^{15}N_{0.4}$, *J. Alloy Compds.* 187 (1992) 145–156.

[13] I. D. Fawcett, K. V. Ramanujachary, M. Greenblatt, Synthesis, structure and Properties of the oxynitrides $SrWO_2N$ and $SrMoO_{2.5}N_{0.5}$, *Mat. Res. Bull.* 32 (1997) 1565–1570.

[14] J. Oró-Solé, L. Clark, W. Bonin, J. P. Attfield, A. Fuertes, Anion-ordered chains in a d^1 perovskite oxynitride: $NdVO_2N$, *Chem. Comm.* 49 (2013) 2430–2432.

[15] T. Bräuniger, T. Müller, A. Pampel, H. -P. Abicht, “Study of oxygen-nitrogen replacement in $BaTiO_3$ by ^{14}N solid-state nuclear magnetic resonance”, *Chem. Mater.* 17 (2005) 4114–4117.

[16] D. Chen, D. Habu, Y. Masubuchi, S. Torii, T. Kamiyama, S. Kikkawa, Partial nitrogen loss in $SrTaO_2N$ and $LaTiO_2N$ oxynitride perovskites, *Solid State Sci.* 54 (2016) 2–6.

[17] T. Motohashi, Y. Hamade, Y. Masubuchi, T. Takeda, K. Murai, A. Yoshiasa, S. Kikkawa, Structural phase transition in the perovskite-type tantalum oxynitride, $Ca_{1-x}Eu_xTa(O,N)_3$, *Mat. Res. Bull.* 44 (2009) 1899–1905.

[18] S.J. Clarke, B.P. Guinot, C.W. Michie, M.J.C. Calmont, M.J. Rosseinsky, Oxynitride perovskites: synthesis and structures of $LaZrO_2N$, $NdTiO_2N$, and $LaTiO_2N$ and comparison with oxide perovskites, *Chem. Mater.* 14 (2002) 288–297.

[19] P. Antoine, R. Assabaa, P. L’Haridon, R. Marchand, Y. Laurent, Transport properties

- of the new perovskite-type $\text{LaVO}_{3-x}\text{N}_x$ oxynitrides, *Mat. Sci. Eng. B5* (1989) 43–46.
- [20] P. Antoine, R. Marchand, Y. Laurent, On the electrical properties of the perovskites $\text{LnWO}_x\text{N}_{3-x}$, *Mat. Res. Bull.* 23 (1988) 953–957.
- [21] R. Marchand, F. Pors, Y. Laurent, Elaboration and characterization of new oxynitrides with a perovskite structure, *Rev. Int. Hautes Temper. Refract.* 23 (1986) 11–15.
- [22] X. Gouin, R. Marchand, Y. Laurent, Infrared dielectric response of BaTaO_2N , *Solid State Commun.* 93 (1995) 857–859.
- [23] Y.-I. Kim, P.M. Woodward, C.-W. Tai, Characterization of the Structural, Optical, and Dielectric Properties of Oxynitride Perovskites AMO_2N ($A = \text{Ba, Sr, Ca}$; $M = \text{Ta, Nb}$), *Chem. Mater.* 16 (2004) 1267–1276.
- [24] K. Page, M. W. Stoltzfus, Y. -I. Kim, T. Proffen, P. M. Woodward, A. K. Cheetham, R. Seshadri, Local atomic ordering in BaTaO_2N studied by neutron pair distribution function analysis and density function theory, *Chem. Mater.* 19 (2007) 4037–4042.
- [25] R.L. Withers, Y. Liu, P.M. Woodward, Y.I. Kim, Structurally frustrated polar nanoregions in BaTaO_2N and the relationship between its high dielectric permittivity and that of BaTiO_3 , *App. Phys. Lett.* 92 (2008) 102907/1-3.
- [26] B. Ravel, Y.I. Kim, P.M. Woodward, C.M. Fang, Role of local disorder in the dielectric response of BaTaO_2N , *Phys. Rev. B* 73 (2006) 184121/1-7.
- [27] Y. Hinuma, H. Moriwake, Y. Zhang, T. Motohashi, S. Kikkawa, I. Tanaka, First principles study on relaxor-type ferroelectric behavior without chemical inhomogeneity in BaTaO_2N and SrTaO_2N , *Chem. Mater.* 24 (2012) 4343–4349.
- [28] H. Wolff, R. Dronskowski, First-Principles and Molecular-Dynamics Study of Structure and Bonding in Perovskite-Type Oxynitrides ABO_2N ($A = \text{Ca, Sr, Ba}$; $B = \text{Ta, Nb}$), *J. Comput. Chem.* 29 (2008) 2260–2267.
- [29] S.H. Porter, X. Huang, P.M. Woodward, Study of Anion Order/Disorder in RTaN_2O ($R = \text{La, Ce, Pr}$) Perovskite Nitride Oxides, *Cryst. Growth Des.* 14 (2014) 117–125.
- [30] Y.-R. Zhang, T. Motohashi, Y. Masubuchi, S. Kikkawa, Local anionic ordering and anisotropic displacement in dielectric perovskite SrTaO_2N , *J. Ceram. Soc. Jpn.* 119 (2011) 581–586.
- [31] M. Yang, J. Oró-Solé, J. A. Rodgers, A. B. Jorge, A. Fuertes, J. P. Attfield, Anion order in perovskite oxynitrides, *Nat. Chem.* 3 (2011) 47–52.
- [32] A. Hosono, Y. Masubuchi, S. Yasui, M. Takesada, T. Endo, M. Higuchi, M. Itoh, S. Kikkawa, Ferroelectric BaTaO_2N Crystals Grown in a BaCN_2 Flux, *Inorg. Chem.* 58 (2019) 16752–16760.
- [33] C.M. Fang, G.A. de Wijs, E. Orhan, G. de With, R.A. de Groot, H.T. Hintzen, R.

Marchand, Local structure and electrical properties of BaTaO₂N with perovskite-type structure, *J. Phys. Chem. Solids*, 64 (2003) 281-286.

[34] Y. Masubuchi, S. -K. Sun, S. Kikkawa, Processing of dielectric oxynitride perovskites for powders, ceramics, compacts and thin films, *Dalton Trans.* 44 (2015) 10570–10581.

[35] A. Hosono, S.-K. Sun, Y. Masubuchi, S. Kikkawa, Additive sintering and post-ammonolysis of dielectric BaTaO₂N oxynitride perovskite, *J. Eur. Ceram. Soc.* 36 (2016) 3341–3345.

[36] Y.-R. Zhang, T. Motohashi, Y. Masubuchi, S. Kikkawa, Sintering and Dielectric Properties of Perovskite SrTaO₂N Ceramics, *J. Eur. Ceram. Soc.* 32 (2012) 1269–1274.

[37] S.-K. Sun, Y.-R. Zhang, Y. Masubuchi, T. Motohashi, S. Kikkawa, Additive sintering, postannealing, and dielectric properties of SrTaO₂N, *J. Am. Ceram. Soc.* 97 (2014) 1023–1027.

[38] A. Hosono, Y. Masubuchi, S. Kikkawa, Sintering behavior of dielectric SrTaO₂N under high pressure of nitrogen, *Ceram. Int.* 43 (2017) 2737–2742.

[39] H. Takeuchi, D. Miyamoto, Y. Masubuchi, M. Higuchi, K. Ishii, T. Uchikoshi, Preparation of thick dense ceramic films of dielectric BaTaO₂N thorough electrophoretic deposition, *Ceram. Int.* 49 (2023) 21825–21829.

[40] A. Hosono, M. Inoguchi, Y. Masubuchi, K. Murayama, M. Iha, M. Higuchi, S. Kikkawa, Spark Plasma Sintering of Dielectric BaTaO₂N close to the Melting Point of the BaCN₂ Additive, *J. Eur. Ceram. Soc.* 40 (2020) 2317–2322.

[41] H. Yamane, M. Shimada, S. J. Clarke, F. J. DiSalvo, Preparation of GaN Single Crystals Using a Na Flux, *Chem. Mater.* 9 (1997) 413–416.

[42] H. Yamane, F. J. DiSalvo, Sodium flux synthesis of nitrides, *Prog. Solid State Chem.* 51 (2018) 27–40.

[43] G. Wang, J. Jian, W. Yuan, X. Chen, Growth of GaN Single Crystals Using Ca-Li₃N Composite Flux, *Cryst. Growth Des.* 6 (2006) 1157–1160.

[44] C.O. Dugger, “The synthesis of aluminum nitride single crystals, *Mat. Res. Bull.* 9 (1974) 331–336.

[45] T. Taniguchi, S. Yamaoka, Spontaneous nucleation of cubic boron nitride single crystal by temperature gradient method under high pressure, *J. Cryst. Growth* 222 (2001) 549–547.

[46] T. Taniguchi, K. Watanabe, Synthesis of high-purity boron nitride single crystals under high pressure by using Ba-BN solvent, *J. Cryst. Growth* 303 (2007) 525–529.

[47] K. Ishida, C. Tassel, D. Kato, H. Ubukakta, K. Murayama, T. Murakami, M. Yashima, Y. Higo, Y. Tange, W. A. Phelan, T. M. McQueen, H. Kageyama, Highly Electron-Doped

- TaON Single-Crystal Growth by a High-Pressure Flux Method, *Inorg. Chem.* 61 (2022) 11118–11123.
- [48] M. Hojamberdiev, K. Yubuta, J. J. M. Vequizo, A. Yamanaka, S. Oishi, K. Domen, K. Teshima, NH₃-assisted flux growth of cube-like BaTaO₂N submicron crystals in a completely ionized nonaqueous high-temperature solution and their water splitting activity, *Cryst. Growth Des.* 15 (2015) 4663–4671.
- [49] M. Hojamberdiev, A. Yamaguchi, K. Yubuta, S. Oishi, K. Teshima, Fabrication of La₂Ti₂O₇ Crystals Using an Alkali-Metal Molibdate Flux Growth Method and Their Nitridability To Form LaTiO₂N Crystals under a High-Temperature NH₃ atmosphere, *Inorg. Chem.* 54 (2015) 3237–3244.
- [50] N. Cordes, T. Bräuniger, W. Schnick, Ammonothermal Synthesis of *E*AMO₂N (*E*A = Sr, Ba; *M* = Nb, Ta) Perovskites and ¹⁴N Solid-State NMR Spectroscopic Investigations of *AM*(O,N)₃ (*A* = Ca, Sr, Ba, La), *Eur. J. Inorg. Chem.* 2018 (2018) 5019–5026.
- [51] N. Cordes, W. Schnick, Ammonothermal Synthesis of Crystalline Oxonitride Perovskites *Ln*TaON₂ (*Ln* = La, Ce, Pr, Nd, Sm, Gd), *Chem. Eur. J.* 23 (2017) 11410–11415.
- [52] C. Izawa, T. Kobayashi, K. Kishida, T. Watanabe, Ammonothermal Synthesis and Photocatalytic Activity of Lower Valence Cation-Doped LaNbON₂, *Adv. Mat. Sci. Engin.* 2014 (2014) 465720/1-5.
- [53] A. Hosono, Y. Masubuchi, T. Endo, S. Kikkawa, Molten BaCN₂ for the sintering and crystal growth of dielectric oxynitride perovskites Sr_{1-x}Ba_xTaO₂N (*x* = 0.04 – 0.23), *Dalton Trans.* 46 (2017) 16837–16844.
- [54] A. Perret, A. M. Krawczynski, Recherches sur les cyanamides métalliques, *Helv. Chim. Acta* 15 (1932) 1009–1022.
- [55] S. Nagai, G. Yamaguchi, Studies on Synthesis of Calcium Cyanamide from Calcium Carbonate and Ammonia, I, *J. Soc. Chem. Ind. Japan* 43 (1940) 219B.
- [56] Y. Masubuchi, S. Nishitani, A. Hosono, Y. Kitagawa, J. Ueda, S. Tanabe, H. Yamane, M. Higuchi, and S. Kikkawa, Red-emission over a wide range of wavelengths at various temperatures from tetragonal BaCN₂:Eu²⁺, *J. Mater. Chem. C* 6 (2018) 6370–6377.
- [57] A. Hosono, R. P. Stoffel, Y. Masubuchi, R. Dronskowski, S. Kikkawa, Melting Behavior of Alkaline-Earth Metal Carbodiimides and Their Thermochemistry from First-Principles, *Inorg. Chem.* 58 (2019) 8938–8942.
- [58] K. Momma, F. Izumi, VESTA 3 for three-dimensional visualization of crystal, volumetric and morphology data, *J. Appl. Crystallogr.* 44 (2011) 1272–1276.
- [59] D. Seol, B. Kim, Y. Kim, Non-piezoelectric effects in piezoresonance force microscopy, *Curr. Appl. Phys.* 17 (2017) 661–674.

- [60] N. Faraji, Z. Yan, J. Seidel, Electrical conduction at domain walls in lead titanate (PbTiO_3) single crystals, *Appl. Phys. Lett.* 110 (2017) 213108/1-5.
- [61] J. Seidel, L. W. Martin, Q. He, Q. Zhan, Y. -H. Chu, A. Rother, M. E. Hawkrigde, P. Maksymovych, P. Yu, M. Gajek, N. Balke, S. V. Kalinin, S. Gemming, F. Wang, G. Catalan, J. F. Scott, N. A. Spaldin, J. Orestein, R. Ramesh, Conduction at domain walls in oxide multiferroics, *Nat. Mater.* 8 (2009) 229–234.
- [62] A. Hosono, Y. Masubuchi, Y. Nagamine, T. Shibahara, S. Kikkawa, Piezoresponse and microstructure of BaTaO_2N ceramics, *J. Eur. Ceram. Soc.* 38 (2018) 3478–3482.
- [63] W.J. Merz, Domain formation and domain wall motions in ferroelectric BaTiO_3 single crystals, *Phys. Rev.*, 95 (1954) 690-698.
- [64] D. Fu, H. Taniguchi, M. Itoh, S. Koshihara, N. Yamamoto, S. Mori, Relaxor $\text{Pb}(\text{Mg}_{1/3}\text{Nb}_{2/3})\text{O}_3$: A ferroelectric with multiple inhomogeneities, *Phys. Rev. Lett.*, 103 (2009) 207601/1-4.
- [65] S. Kikkawa, S. -K. Sun, Y. Masubuchi, Y. Nagamine, T. Shibahara, Ferroelectric response induced by *cis*-type anion ordering in SrTaO_2N oxynitride perovskite, *Chem. Mater.* 28 (2016) 1312–1317.
- [66] A. Rachel, S. G. Ebbinghaus, M. Güngerich, P. J. Klar, J. Hanss, A. Weidenkaff, A. Reller, Tantalum and niobium perovskite oxynitrides Synthesis and analysis of the thermal behavior, *Thermochimica Acta*, 438 (2005) 134 – 143.
- [67] R. Aguiar, D. Logvinovich. A. Weidenkaff, A. Reller, S. G. Ebbinghaus, Thermal oxidation of oxynitride perovskites in different atmospheres, *Thermochimica Acta* 471 (2008) 55 – 60.
- [68] Y. Masubuchi, D. Miyamoto, M. Higuchi, B_2O_3 as a new sintering additive for perovskite-type SrTaO_2N oxynitride ceramics, *J. Asian Ceram. Soc.* 10 (2022) 158 – 164.
- [69] P. Sarkar, P. S. Nicholson, Electrophoretic deposition (EPD): mechanisms, kinetics, and application to ceramics. *J. Am. Ceram. Soc.* 79 (1996) 1987-2002.
- [70] F. Tang, T. Uchikoshi, K. Ozawa, Y. Sakka, Effect of polyethyleneimine on the dispersion and electrophoretic deposition of nano-sized titania aqueous suspensions. *J. Eur. Ceram. Soc.* 26 (2006) 1555-1560.
- [71] H. Yu, Q. Chen, Z. Jin, Thermodynamic reassessment of the BaO - B_2O_3 system, *J. Phase Equil.* 20 (1999) 479–484.
- [72] W. Li, E. Olevski, J. McKittrick, A. L. Maximenko, R. M. German, Densification mechanisms of spark plasma sintering: multi-step pressure dilatometry, *J. Mater. Sci.* 47 (2012) 7036–7046.
- [73] R. Chaim, G. Chevallier, A. Weidel, C. Estournés, Grain growth during spark plasma and flash sintering of ceramic nanoparticles: a review, *J. Mater. Sci.* 53 (2018) 3087–3105.

- [74] M.J. Li, L.M. Zhang, Q. Shen, T. Li, M. Q. Yu, Microstructure and properties of spark plasma sintered AlN ceramics, *J. Mater. Sci.*, 41 (2006) 7934–7938.
- [75] D. Salamon, Z. Shen, P. Sajgalik, Rapid formation of α -sialon during spark plasma sintering: Its origin and implications, *J. Eur. Ceram. Soc.* 27 (2007) 2541–2547.
- [76] Z. Shen, M. Nygren, Microstructural Prototyping of Ceramics by Kinetic Engineering: Applications of Spark Plasma Sintering, *Chem. Rec.* 5 (2005) 173–184.
- [77] D. Li, W. Li, C. Fasel, J. Shen, R. Riedel, Sinterability of the oxynitride LaTiO₂N with perovskite-type structure, *J. Alloys Compds.* 586 (2014) 567–573.
- [78] Y. Masubuchi, K. Koyama, A. Hosono, M. Tekesada, M. Higuchi, S. Kikkawa, *Cis* TaO₄N₂ octahedral chains extend to 50 nm domains forming an average cubic lattice in BaTaO₂N crystal lattice, in preparation.